

Roberto Bergamaschini

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

40
papers

604
citations

14
h-index

23
g-index

45
ext. papers

691
ext. citations

5.1
avg, IF

3.67
L-index

#	Paper	IF	Citations
40	Growth of thick [111]-oriented 3C-SiC films on T-shaped Si micropillars. <i>Materials and Design</i> , 2021 , 109883		2
39	Prismatic Ge-rich inclusions in the hexagonal SiGe shell of GaP-Si-SiGe nanowires by controlled faceting. <i>Nanoscale</i> , 2021 , 13, 9436-9445	7.7	
38	Faceting of Si and Ge crystals grown on deeply patterned Si substrates in the kinetic regime: phase-field modelling and experiments. <i>Scientific Reports</i> , 2021 , 11, 18825	4.9	1
37	Sunburst pattern by kinetic segregation in core-shell nanowires: A phase-field study. <i>Applied Surface Science</i> , 2020 , 517, 146056	6.7	4
36	Self-Assembly of Nanovoids in Si Microcrystals Epitaxially Grown on Deeply Patterned Substrates. <i>Crystal Growth and Design</i> , 2020 , 20, 2914-2920	3.5	2
35	Selective Area Epitaxy of GaAs/Ge/Si Nanomembranes: A Morphological Study. <i>Crystals</i> , 2020 , 10, 57	2.3	4
34	Kinetic Control of Morphology and Composition in Ge/GeSn Core/Shell Nanowires. <i>ACS Nano</i> , 2020 , 14, 2445-2455	16.7	12
33	Reentrant Behavior of the Density vs. Temperature of Indium Islands on GaAs(111)A. <i>Nanomaterials</i> , 2020 , 10,	5.4	1
32	Strain engineering in Ge/GeSn core/shell nanowires. <i>Applied Physics Letters</i> , 2019 , 115, 113102	3.4	14
31	Growth and Coalescence of 3C-SiC on Si(111) Micro-Pillars by a Phase-Field Approach. <i>Materials</i> , 2019 , 12,	3.5	5
30	Motion of crystalline inclusions by interface diffusion in the proximity of free surfaces. <i>Journal of Nanoparticle Research</i> , 2019 , 21, 1	2.3	1
29	Competition Between Kinetics and Thermodynamics During the Growth of Faceted Crystal by Phase Field Modeling. <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1800518	1.3	17
28	Slip trace-induced terrace erosion. <i>Applied Surface Science</i> , 2019 , 466, 454-458	6.7	
27	Morphological evolution of Ge/Si nano-strips driven by Rayleigh-like instability. <i>Applied Physics Letters</i> , 2018 , 112, 022101	3.4	9
26	Critical strain for Sn incorporation into spontaneously graded Ge/GeSn core/shell nanowires. <i>Nanoscale</i> , 2018 , 10, 7250-7256	7.7	24
25	Optically reconfigurable polarized emission in Germanium. <i>Scientific Reports</i> , 2018 , 8, 11119	4.9	6
24	Growth kinetics and morphological analysis of homoepitaxial GaAs fins by theory and experiment. <i>Physical Review Materials</i> , 2018 , 2,	3.2	20

23	Dislocation-Free SiGe/Si Heterostructures. <i>Crystals</i> , 2018 , 8, 257	2.3	13
22	Solving the critical thermal bowing in 3C-SiC/Si(111) by a tilting Si pillar architecture. <i>Journal of Applied Physics</i> , 2018 , 123, 185703	2.5	5
21	Phase-field simulations of faceted Ge/Si-crystal arrays, merging into a suspended film. <i>Applied Surface Science</i> , 2017 , 391, 33-38	6.7	16
20	A self-ordered, body-centered tetragonal superlattice of SiGe nanodot growth by reduced pressure CVD. <i>Nanotechnology</i> , 2017 , 28, 485303	3.4	5
19	Modeling the competition between elastic and plastic relaxation in semiconductor heteroepitaxy: From cyclic growth to flat films. <i>Physical Review B</i> , 2016 , 94,	3.3	14
18	Continuum modelling of semiconductor heteroepitaxy: an applied perspective. <i>Advances in Physics: X</i> , 2016 , 1, 331-367	5.1	13
17	Temperature-controlled coalescence during the growth of Ge crystals on deeply patterned Si substrates. <i>Journal of Crystal Growth</i> , 2016 , 440, 86-95	1.6	11
16	Kinetic growth mode of epitaxial GaAs on Si(001) micro-pillars. <i>Journal of Applied Physics</i> , 2016 , 120, 245702	3.2	10
15	Reduced-Pressure Chemical Vapor Deposition Growth of Isolated Ge Crystals and Suspended Layers on Micrometric Si Pillars. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 26374-26380	9.5	9
14	Dynamics of pit filling in heteroepitaxy via phase-field simulations. <i>Physical Review B</i> , 2016 , 94,	3.3	14
13	Faceting of Equilibrium and Metastable Nanostructures: A Phase-Field Model of Surface Diffusion Tackling Realistic Shapes. <i>Crystal Growth and Design</i> , 2015 , 15, 2787-2794	3.5	54
12	Engineered Coalescence by Annealing 3D Ge Microstructures into High-Quality Suspended Layers on Si. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 19219-25	9.5	23
11	3D heteroepitaxy of mismatched semiconductors on silicon. <i>Thin Solid Films</i> , 2014 , 557, 42-49	2.2	16
10	Epitaxial Ge-crystal arrays for X-ray detection. <i>Journal of Instrumentation</i> , 2014 , 9, C03019-C03019	1	4
9	The interplay of morphological and compositional evolution in crystal growth: a phase-field model. <i>Philosophical Magazine</i> , 2014 , 94, 2162-2169	1.6	9
8	Ge Crystals on Si Show Their Light. <i>Physical Review Applied</i> , 2014 , 1,	4.3	28
7	(Invited) Three-Dimensional Epitaxial Si _{1-x} Ge _x , Ge and SiC Crystals on Deeply Patterned Si Substrates. <i>ECS Transactions</i> , 2014 , 64, 631-648	1	12
6	A Structural Characterization of GaAs MBE Grown on Si Pillars. <i>Acta Physica Polonica A</i> , 2014 , 125, 986-990	6	2

5	Self-aligned Ge and SiGe three-dimensional epitaxy on dense Si pillar arrays. <i>Surface Science Reports</i> , 2013 , 68, 390-417	12.9	36
4	Scaling hetero-epitaxy from layers to three-dimensional crystals. <i>Science</i> , 2012 , 335, 1330-4	33.3	125
3	Anomalous smoothing preceding island formation during growth on patterned substrates. <i>Physical Review Letters</i> , 2012 , 109, 156101	7.4	34
2	Temperature-dependent evolution of the wetting layer thickness during Ge deposition on Si(001). <i>Nanotechnology</i> , 2011 , 22, 285704	3.4	15
1	Optimal Growth Conditions for Selective Ge Islands Positioning on Pit-Patterned Si(001). <i>Nanoscale Research Letters</i> , 2010 , 5, 1873-7	5	12